

T-58-07

KA431

## LINEAR INTEGRATED CIRCUIT

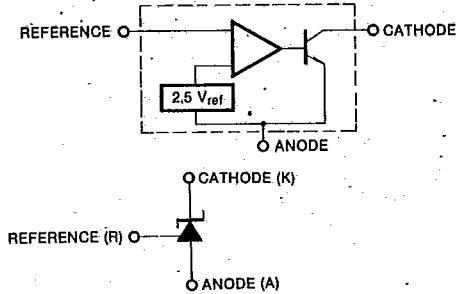
## PROGRAMMABLE PRECISION REFERENCES

The KA431 is a three-terminal adjustable regulator series with guaranteed thermal stability over applicable temperature ranges. The output voltage may be set to any value between  $V_{ref}$  (approximately 2.5 volts) and 36 volts with two external resistors. These devices have a typical dynamic output impedance of 0.2Ω. Active output circuitry provides a very sharp turn-on characteristic, making these devices excellent replacement for zener diodes in many applications.

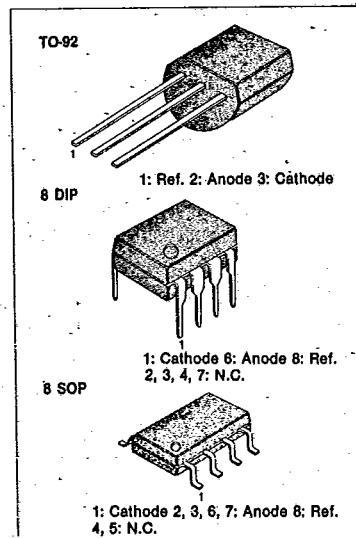
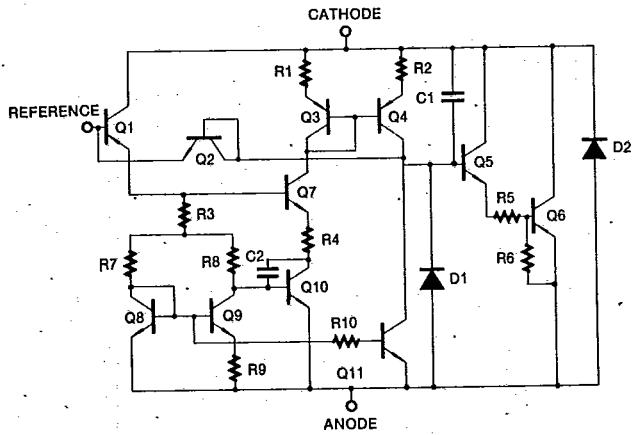
## FEATURES

- Programmable output voltage to 36 volts
- Low dynamic output Impedance 0.2Ω typical
- Sink current capability of 1.0 to 100mA
- Equivalent full-range temperature coefficient of 50ppm/°C typical
- Temperature compensated for operation over full rated operating temperature range
- Low output noise voltage

## BLOCK DIAGRAM



## SCHEMATIC DIAGRAM



## ORDERING INFORMATION

Device	Operating Temperature	Package
KA431CZ	0 ~ + 70°C	TO-92
**KA431CN	0 ~ + 70°C	8 DIP
KA431CD	0 ~ + 70°C	8 SOP
**KA431IZ	- 40 ~ + 85°C	TO-92
**KA431IN	- 40 ~ + 85°C	8 DIP

\*\* Under Development.



SAMSUNG SEMICONDUCTOR

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## ABSOLUTE MAXIMUM RATINGS

(Operating temperature range applies unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Cathode Voltage	$V_{KA}$	37	V
Cathode Current Range (Continuous)	$I_K$	-100 ~ +150	mA
Reference Input Current Range	$I_{ref}$	0.05 ~ +10	mA
Power Dissipation	$P_D$		
D, Z Suffix Package		770	mW
N Suffix Package		1000	mW
Operating Temperature	$T_{opr}$		
KA431CZ, KA431CN, KA431CD		0 ~ +70	°C
KA431IZ, KA431IN		-40 ~ +85	°C
Operating Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{stg}$	-65 ~ +150	°C

## RECOMMENDED OPERATING CONDITIONS

Characteristic	Symbol	Min	Typ	Max	Unit
Cathode Voltage	$V_{KA}$	$V_{ref}$		36	V
Cathode Current	$I_K$	1.0		100	mA

## ELECTRICAL CHARACTERISTICS (Ta = 25°C, unless otherwise specified)

Characteristic	Symbol	Test Conditions		Min	Typ	Max	Unit	*T/C
Reference Input Voltage	$V_{ref}$	$V_{KA} = V_{ref}$	$T_a = 25^\circ C$	2.440	2.495	2.550	V	1
		$I_K = 10mA$	$T_a = 0^\circ C$ to $70^\circ C$	2.423		2.567		
Deviation of Reference Input Voltage Over Temperature 1	$V_{ref(dev)}$	$V_{KA} = V_{ref}$ , $I_K = 10mA$	$T_a = 0^\circ C$ to $70^\circ C$		8	17	mV	1
Ratio of Change in Reference Input Voltage to the Change in Cathode Voltage	$\frac{V_{ref}}{V_{KA}}$	$I_K = 10mA$	$V_{KA} = V_{ref}$ to $10V$		-1.4	-2.7	mV/V	2
			$V_{KA} = 10V$ to $36V$		-1.0	-2.0		
Reference Input Current	$I_{ref}$	$I_K = 10mA$ $R1 = 10K\Omega$ $R2 = \infty$	$T_a = 25^\circ C$		1.8	4.0	$\mu A$	2
			$T_a = 0^\circ C$ to $70^\circ C$			5.2		
Reference Input Current Deviation Over Temperature Range	$I_{ref}$	$I_K = 10mA$ , $R1 = 10K\Omega$ $R2 = \infty$ $T_a = 0^\circ C$ to $70^\circ C$			0.4	1.2	$\mu A$	2
Minimum Cathode Current for Regulation	$I_{Kmin}$	$V_{KA} = V_{ref}$			0.5	1.0	mA	1
Off-State Cathode Current	$I_{Koff}$	$V_{KA} = 36V$ , $V_{ref} = 0V$			2.6	1000	nA	3
Dynamic Impedance 2	$Z_{KA}$	$V_{KA} = V_{ref}$ $I_K = 1.0$ to $100mA$ $f \leq 1.0KHz$			0.22	0.5	$\Omega$	1

\* Test Circuit



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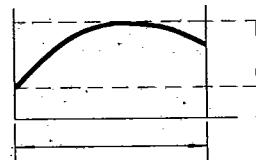
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## LINEAR INTEGRATED CIRCUIT

Note: 1. The deviation parameters  $V_{ref(dev)}$  and  $I_{ref(dev)}$  are defined as the differences between the maximum and minimum values obtained over the rated temperature range. The equivalent full-range temperature coefficient of the reference input voltage,  $aV_{ref}$ , is defined as:

$$\text{Max } V_{ref} \text{ Min } V_{ref} \Delta T_A V_{ref(dev)}$$

$$aV_{ref} \left( \frac{\text{ppm}}{^\circ\text{C}} \right) = \frac{\left( \frac{V_{ref(dev)}}{V_{ref@25^\circ\text{C}}} \right) \times 10^6}{\Delta T_A}$$



where  $\Delta T_A$  is the rated operating free-air temperature range of the device.  
 $aV_{ref}$  can be positive or negative depending on whether minimum  $V_{ref}$  or maximum  $V_{ref}$ , respectively, occurs at the lower temperature

Example: Max  $V_{ref} = 2500\text{mV}@30^\circ\text{C}$ , Min  $V_{ref} = 2492\text{mV}@0^\circ\text{C}$ ,  $V_{ref} = 2495\text{mV}@25^\circ\text{C}$ ,  $\Delta T_A = 70^\circ\text{C}$  for KA431C

$$aV_{ref} = \frac{\left( \frac{8\text{mV}}{2495\text{mV}} \right) \times 10^6}{70^\circ\text{C}} = 46\text{ppm}/^\circ\text{C}$$

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Because minimum  $V_{ref}$  occurs at the lower temperature, the coefficient is positive.

2. The dynamic impedance is defined as:

$$Z_{KA} = \frac{\Delta V_{KA}}{\Delta I_K}$$

When the device is operated with two external resistors (see Figure 2), the total dynamic impedance of the circuit is given by:

$$Z' = \frac{\Delta V}{\Delta I} = Z_{KA} \left( 1 + \frac{R_1}{R_2} \right)$$

## TEST CIRCUIT

Fig. 1 Test Circuit for  $V_{KA} = V_{ref}$

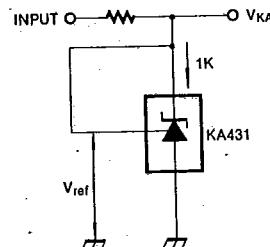
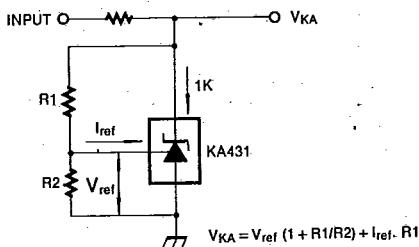
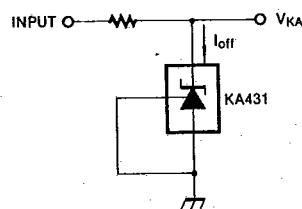


Fig. 2 Test Circuit for  $V_{KA} \geq V_{ref}$



$$V_{KA} = V_{ref} \left( 1 + \frac{R_1}{R_2} \right) + I_{ref} \cdot R_1$$

Fig. 3 Test Circuit for  $I_{off}$



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## TYPICAL PERFORMANCE CHARACTERISTICS

CATHODE CURRENT VS CATHODE VOLTAGE

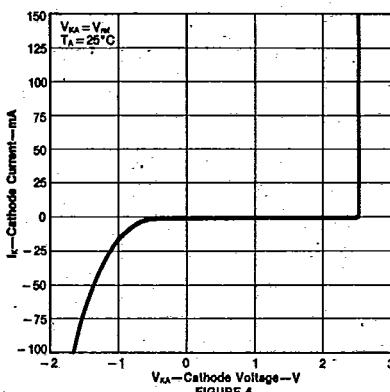


FIGURE 4

CATHODE CURRENT VS CATHODE VOLTAGE

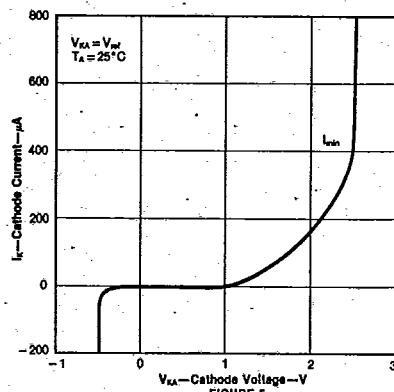


FIGURE 5

CHANGE IN REFERENCE INPUT VOLTAGE VS CATHODE VOLTAGE

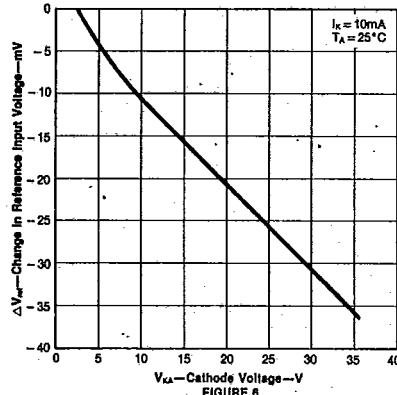


FIGURE 6

NOISE VOLTAGE VS FREQUENCY

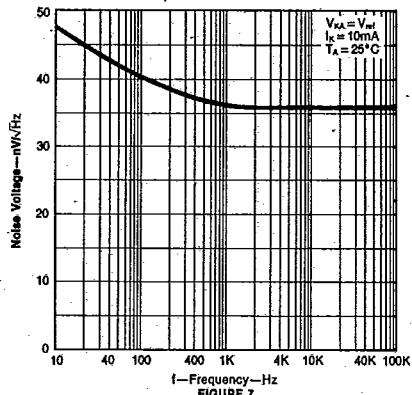


FIGURE 7

DYNAMIC IMPEDANCE VS FREQUENCY

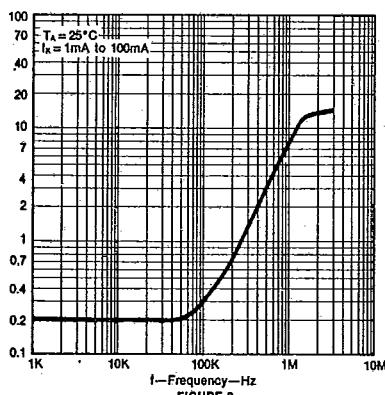


FIGURE 8

SMALL SIGNAL VOLTAGE AMPLIFICATION VS FREQUENCY

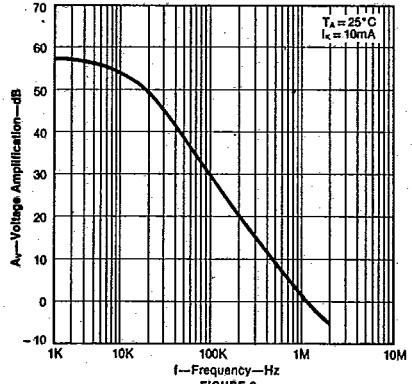


FIGURE 9

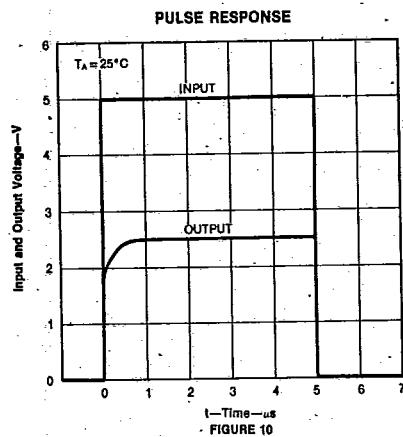


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## TYPICAL PERFORMANCE CHARACTERISTICS (Continued)



## TYPICAL APPLICATIONS

FIGURE 11—SHUNT REGULATOR

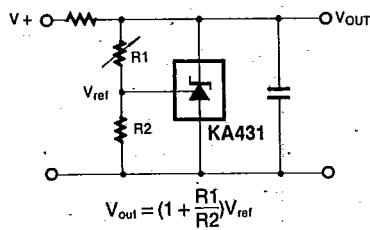


FIGURE 12—SINGLE-SUPPLY COMPARATOR WITH TEMPERATURE-COMPENSATED THRESHOLD

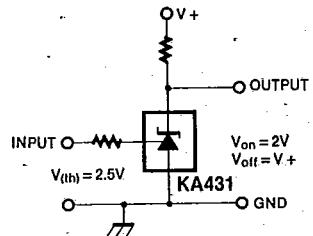


FIGURE 13—SERIES REGULATOR

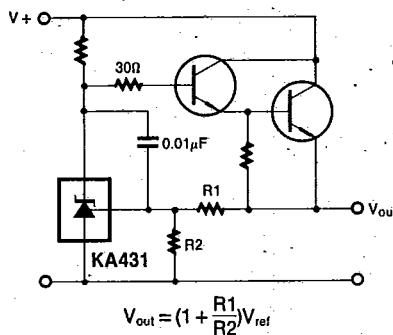


FIGURE 14—OUTPUT CONTROL OF A THREE-TERMINAL FIXED REGULATOR

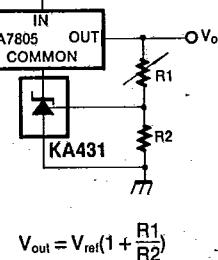
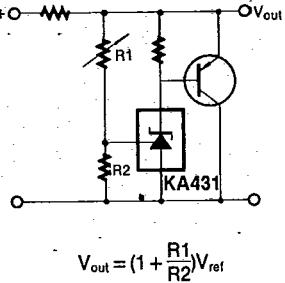


FIGURE 15—HIGHER-CURRENT SHUNT REGULATOR



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## TYPICAL APPLICATIONS (Continued)

FIGURE 16—CROW BAR

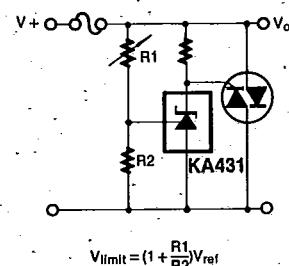


FIGURE 17—OVER-VOLTAGE/UNDER-VOLTAGE PROTECTION CIRCUIT

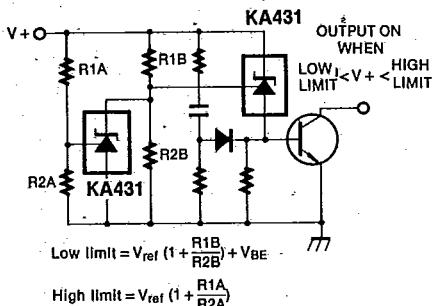


FIGURE 18—VOLTAGE MONITOR

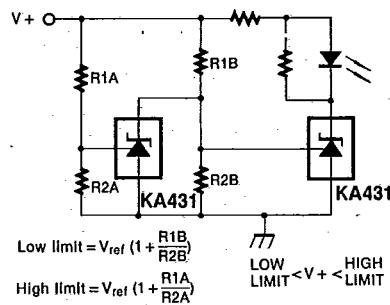


FIGURE 19—DELAY TIMER

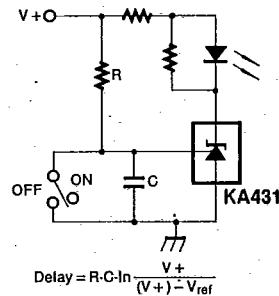


FIGURE 20—CURRENT LIMITER OR CURRENT SOURCE

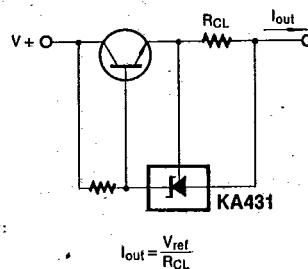
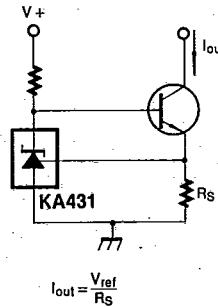


FIGURE 21—CONSTANT-CURRENT SINK



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